

# Weisheng Li

## List of Publications by Year in descending order

Source: <https://exaly.com/author-pdf/11893605/publications.pdf>

Version: 2024-02-01

12  
papers

1,060  
citations

1478505

6  
h-index

1588992

8  
g-index

12  
all docs

12  
docs citations

12  
times ranked

929  
citing authors

#	ARTICLE	IF	CITATIONS
1	Uniform nucleation and epitaxy of bilayer molybdenum disulfide on sapphire. <i>Nature</i> , 2022, 605, 69-75.	27.8	174
2	A compact model for transition metal dichalcogenide field effect transistors with effects of interface traps. <i>Science China Information Sciences</i> , 2021, 64, 1.	4.3	2
3	Sub-thermionic, ultra-high-gain organic transistors and circuits. <i>Nature Communications</i> , 2021, 12, 1928.	12.8	83
4	Reliability of Ultrathin High $\epsilon$ Dielectrics on 2D Semiconductors. , 2021, , .		0
5	Epitaxial growth of wafer-scale molybdenum disulfide semiconductor single crystals on sapphire. <i>Nature Nanotechnology</i> , 2021, 16, 1201-1207.	31.5	339
6	Three-dimensional monolithic micro-LED display driven by atomically thin transistor matrix. <i>Nature Nanotechnology</i> , 2021, 16, 1231-1236.	31.5	120
7	High-Performance CVD MoS <sub>2</sub> Transistors with Self-Aligned Top-Gate and Bi Contact. , 2021, , .		13
8	Bi <sub>2</sub> O <sub>2</sub> Se/Au-Based Schottky Phototransistor With Fast Response and Ultrahigh Responsivity. <i>IEEE Electron Device Letters</i> , 2020, 41, 1464-1467.	3.9	5
9	Reliability of Ultrathin High- $\epsilon$ Dielectrics on Chemical-vapor Deposited 2D Semiconductors. , 2020, , .		5
10	Sensitive and Ultrabroadband Phototransistor Based on Two-Dimensional Bi <sub>2</sub> O <sub>2</sub> Se Nanosheets. <i>Advanced Functional Materials</i> , 2019, 29, 1905806.	14.9	106
11	Uniform and ultrathin high- $\epsilon$ gate dielectrics for two-dimensional electronic devices. <i>Nature Electronics</i> , 2019, 2, 563-571.	26.0	204
12	Toward High-mobility and Low-power 2D MoS <sub>2</sub> Field-effect Transistors. , 2018, , .		9